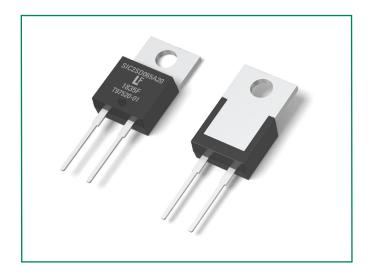


# LSIC2SD065A20A 650 V, 20 A SiC Schottky Barrier Diode









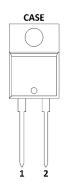
### **Description**

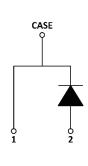
This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

#### **Features**

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

### Circuit Diagram TO-220-2L





#### **Applications**

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

#### **Environmental**

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = P Pb-free lead plating

## **Maximum Ratings**

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	-	650	V	
DC Blocking Voltage	V <sub>R</sub>	T <sub>J</sub> = 25 °C	650	V	
Continuous Forward Current	I <sub>F</sub>	T <sub>c</sub> = 25 °C	45	А	
		T <sub>C</sub> = 135 °C	20		
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	$T_{\rm C} = 25  {\rm ^{\circ}C}$ , $T_{\rm P} = 10  {\rm ms}$ , Half sine pulse	90	А	
Power Dissipation	P <sub>Tot</sub>	T <sub>c</sub> = 25 °C	135	W	
		T <sub>C</sub> = 110 °C	60		
Operating Junction Temperature	T <sub>J</sub>	-	-55 to 175	°C	
Storage Temperature	T <sub>STG</sub>	-	-55 to 150	°C	
Soldering Temperature	T <sub>SOLD</sub>	-	260	°C	

## GEN2 SiC Schottky Diode LSIC2SD065A20A, 650 V, 20 A, TO-220-2L

## Electrical Characteristics (T<sub>J</sub> =25 °C unless otherwise specified)

			Value			
Characteristics	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Voltago	\/	I <sub>F</sub> = 20 A, T <sub>J</sub> = 25 °C	-	1.5	1.8	V
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 20 A, T <sub>J</sub> = 175 °C	-	1.85	-	
Reverse Current	I <sub>R</sub>	$V_R = 650  \text{V}$ , $T_J = 25  ^{\circ}\text{C}$	-	<1	50	μΑ
		$V_{_{\rm R}} = 650  \text{V}$ , $T_{_{\rm J}} = 175  ^{\circ}\text{C}$	-	60	-	
Total Capacitance (	С	$V_R = 1 V, f = 1 MHz$	-	960	-	
		$V_R = 200  V$ , $f = 1  MHz$	-	120	-	pF
		$V_R = 400  \text{V},  \text{f} = 1  \text{MHz}$	-	86	-	
Total Capacitive Charge	Q <sub>c</sub>	$V_R = 400 \text{ V},  Q_c = \int\limits_0^{V_R} c(v) dv$	-	63	-	nC

Thermal Characteristics				
Characteristics	Symbol	Value	Unit	
Thermal Resistance	Raic	1.1	°C/W	

Figure 1: Typical Foward Characteristics

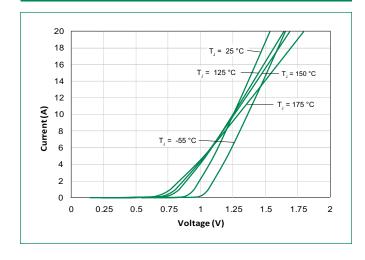
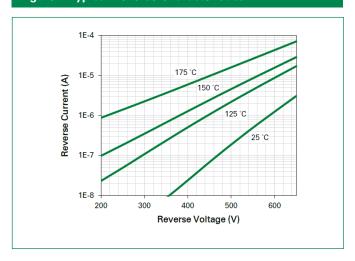


Figure 2: Typical Reverse Characteristics





**Figure 3: Power Derating** 

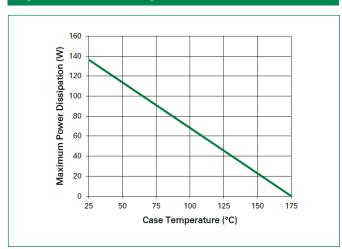


Figure 4: Current Derating

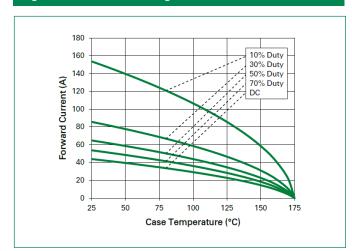


Figure 5: Capacitance vs. Reverse Voltage

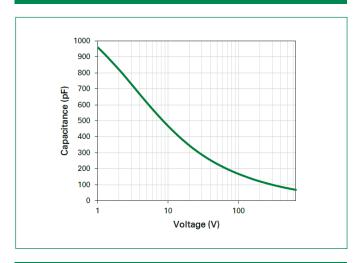


Figure 6: Capacitive Charge vs. Reverse Voltage

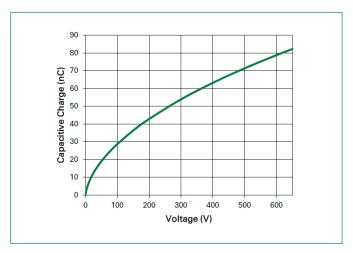


Figure 7: Stored Energy vs. Reverse Voltage

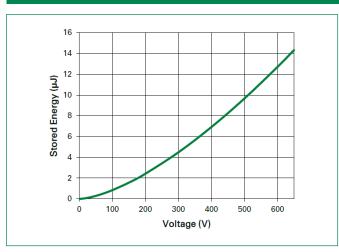
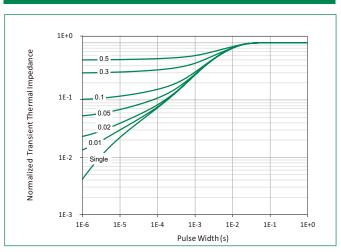
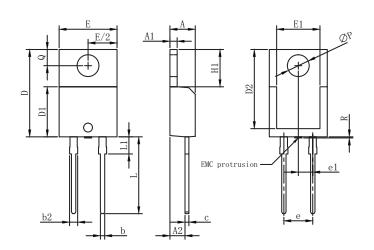


Figure 8: Transient Thermal Impedance

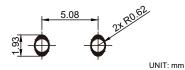


# GEN2 SiC Schottky Diode LSIC2SD065A20A, 650 V, 20 A, TO-220-2L

## Dimensions-Package TO-220-2L

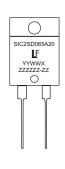


Recommended Solder Pad Layout



Cumbal	Millimeters			
Symbol	Min	Nom	Max	
А	4.32	4.45	4.70	
A1	1.14	1.27	1.40	
A2	2.20	-	2.74	
b	0.69	-	0.90	
b2	1.17	-	1.62	
С	0.36	-	0.60	
D	14.90	-	15.90	
D1	8.62	-	9.40	
D2	12.50	-	12.95	
Е	9.70	10.18	10.36	
E1	7.57	7.61	8.30	
e1	-	2.54	-	
е	5.03	5.08	5.13	
H1	6.30	6.55	6.80	
L	12.88	13.50	14.00	
L1	2.39	-	3.25	
øΡ	3.50	3.84	3.96	
Q	2.65	-	3.05	
R	-	-	0.25	

## **Part Numbering and Marking System**



SIC	= SiC Diode
2	= Gen2
SD	= Schottky Diode
065	= Voltage Rating (650 V)
Α	= TO-220 Package (2 Lead)
20	= Current Rating (20 A)
YY	= Year
WW	= Week
Χ	= Special Code

ZZZZZZ-ZZ = Lot Number

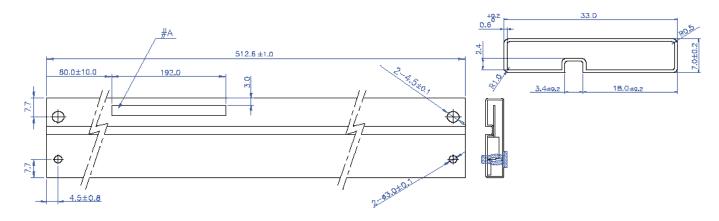
## **Packing Options**

Part Number	Marking	Packing Mode	M.O.Q
L SIC2SD065Δ20Δ	SIC2SD065A20	Tube(50ncs)	1000



## **GEN2 SiC Schottky Diode** LSIC2SD065A20A, 650 V, 20 A, TO-220-2L

#### Packing Specification (Tube for TO-220-2L)



#### [ NOTE ]

- 1. TUBE MATERIAL : PVC / PET (WITH ANTISTATIC COATING)
  - COLOR: TRANSPARENCY, RED, YELLO
  - MARKING #A : BLACK COLOR, LETTER STYLE : Arial
  - Tube Surface Resistance  $:10^6 \sim 10^{11} \,\Omega\,/\text{square}$
  - ESD (Electro Static Discharge) : less than 100 [volts], 6 Months
  - CAMBAR : 1.5 MAX
- 2. PIN COLOR : GREEN (ONE PIN MUST BE INSERTED IN LEFT-SIDE OF "  $\square$  ANTISTATIC~" AND ANOTHER PIN IS FREE.)

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